| PTO/SB/08A (10/01)<br>(Substitute for form 1449A/PTO) | ATTY. DOCKET NO. UMC-96-279 CON<br>Client/Matter No. 81848.0016.001 | APPLICATION NO.: 09/546,174 |
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| INFORMATION DISCLOSURE STATEMENT BY APPLICANT<br>(Use several sheets if necessary)<br>Sheet 1 of 3 | FIRST NAMED INVENTOR:<br>CHIH-CHIEN LIU | |
| | FILING DATE<br>APRIL 11, 2000 | ART UNIT 1711 |



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| EXAMINER SIGNATURE Ruben Lagart | DATE CONSIDERED 6/1/03 |

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